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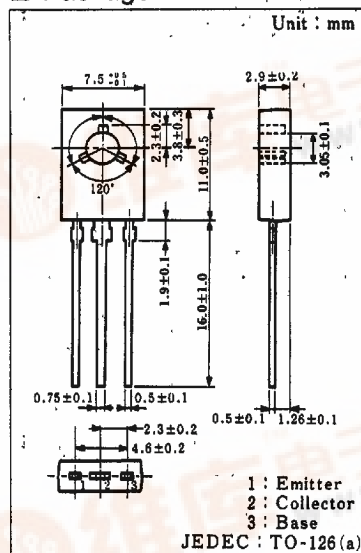
Silicon NPN Epitaxial Planar Type

AF Power Amplifier
For Strobo, Converter

■ Features

- Low collector-emitter saturation voltage ($V_{CE(sat)}$)
- High performance and good operating characteristics at low supply voltage

■ Package Dimensions



■ Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Item	Symbol	Value	Unit
Collector-base voltage	V_{CB0}	40	V
Collector-emitter voltage	V_{CE0}	20	V
Emitter-base voltage	V_{EB0}	7	V
Peak collector current	I_{CP}	7	A
Collector current	I_C	5	A
Collector power dissipation ($T_c=25^\circ\text{C}$)	P_C	10	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	$-55 \sim +150$	$^\circ\text{C}$

■ Electrical Characteristics ($T_c=25^\circ\text{C}$)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CB0}	$V_{CB}=10\text{ V}, I_E=0$			0.1	μA
Collector-emitter voltage	V_{CE0}	$I_C=1\text{ mA}, I_B=0$	20			V
Collector-base voltage	V_{EB0}	$I_E=10\text{ }\mu\text{A}, I_C=0$	7			V
DC current gain	h_{FE1}	$V_{CE}=2\text{ V}, I_C=0.5\text{ A}^*$	140		450	
	h_{FE2}	$V_{CE}=2\text{ V}, I_C=1\text{ A}^*$	70			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=3\text{ A}, I_B=0.1\text{ A}^*$			1	V
Transition frequency	f_T	$V_{CB}=6\text{ V}, I_E=-50\text{ mA}, f=200\text{ MHz}$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB}=20\text{ V}, I_E=0, f=1\text{ MHz}$			50	pF

* Pulse measurement

